

WHAT IS CLAIMED IS:

1. A method for forming a unitized crucible assembly for holding a melt of silicon for forming a silicon ingot by the Czochralski method, the method comprising:

providing a crucible mold, the mold having a channel network comprising:

a bottom channel;

an outer sidewall channel that extends from the bottom channel;

a central weir channel that extends from the bottom channel; and

an inner weir channel that extends from the bottom channel, the central weir channel being disposed between the outer sidewall channel and the inner weir channel;

introducing a slip slurry into the channel network to fill the bottom channel, outer sidewall channel, central weir channel, and inner weir channel with the slip slurry, the slip slurry comprising silica and a liquid carrier;

removing at least a portion of the liquid carrier from the channel network to form a green body;

separating the green body from the crucible mold; and

sintering the green body to dry and densify the green body to form the unitized crucible assembly.

2. The method as set forth in claim 1 wherein the mold comprises a porous body and draws the liquid carrier into the mold by capillary action.

3. The method as set forth in claim 2 wherein the porous body is made of porous silica.

4. The method as set forth in any one of claims 1 to 3 wherein a moisture content of the green body is less than about 50%, less than about 45%, at least about 30 wt%, at least about 35 wt%, at least about 40 wt%, at least about 45 wt%, from about 30 wt% to about 50 wt% or from about 35 wt% to about 45 wt%.

5. The method as set forth in any one of claims 1 to 4 wherein the green body is sintered at a temperature from about 1200°C to about 1800°C, from about 1300°C to about 1700°C, or from about 1300°C to about 1650°C.

6. The method as set forth in any one of claims 1 to 5 wherein the bottom channel, outer sidewall channel, central weir channel and inner weir channel are each fluidly connected to each other.

7. The method as set forth in claim 6 wherein the bottom channel is rounded.

8. The method as set forth in claim 7 wherein the unitized crucible assembly includes a single layer bottom.

9. The method as set forth in any one of claims 1 to 8 wherein the unitized crucible assembly is transparent.

10. The method as set forth in any one of claims 1 to 9 wherein the unitized crucible assembly comprises:

a bottom;

an outer sidewall that extends upward from the bottom;

a central weir that extends upward from the bottom; and

an inner weir that extends upward from the bottom, the central weir being disposed between the outer sidewall and the inner weir.

11. The method as set forth in any one of claims 1 to 10 wherein the slip slurry and/or mold are selected to form a unitized crucible assembly having a concentration of calcium of less than about 1 ppmw, a concentration of sodium of less than about 0.5 ppmw, a concentration of potassium of less than about 0.5 ppmw, a concentration of lithium of less than about 0.5 ppmw, and a concentration of iron of less than about 0.5 ppmw.

12. The method as set forth in claim 11 wherein the mold comprises:

a central weir peg that extends through the central weir channel to form an opening in the central weir of the unitized crucible assembly to allow silicon melt to pass through the central weir; and

an inner weir peg that extends through the inner weir channel to form an opening in the inner weir of the unitized crucible assembly to allow silicon melt to pass through the inner weir.

13. A method for growing a single crystal silicon ingot comprising:

providing a unitized crucible assembly by the method of claim 12;

adding polycrystalline silicon to a crucible melt zone disposed between the outer sidewall and the central weir to form a silicon melt, the silicon melt flowing through the central weir opening to a stabilization zone disposed between the central weir and the inner weir, the silicon melt flowing through the inner weir opening to a growth zone disposed within the inner weir;

contacting the silicon melt within the growth zone with a seed crystal; and

withdrawing the seed crystal from the silicon melt to form a single crystal silicon ingot.

14. A unitized crucible assembly formed by the method of any one of claims 1 to 12, the unitized crucible assembly comprising:

a bottom;

an outer sidewall that extends upward from the bottom;

a central weir that extends upward from the bottom; and

an inner weir that extends upward from the bottom, the central weir being disposed between the outer sidewall and the inner weir.

15. A method for forming a unitized crucible assembly for holding a melt of silicon for forming a

silicon ingot by the Czochralski method, the method comprising:

providing a crucible mold, the mold comprising a porous body and a channel network disposed within the porous body, the channel network comprising:

a bottom channel;

an outer sidewall channel that extends from the bottom channel; and

an inner weir channel that extends from the bottom channel, the inner weir channel being disposed interior to the outer sidewall channel;

introducing a slip slurry into the channel network to fill the bottom channel, outer sidewall channel and inner weir channel with the slip slurry, the slip slurry comprising silica and a liquid carrier;

drawing at least a portion of the liquid carrier into the mold by capillary action to form a green body;

separating the green body from the crucible mold; and

sintering the green body to dry and densify the green body to form the unitized crucible assembly.

16. The method as set forth in claim 15 wherein the mold comprises a porous body and draws the liquid carrier into the mold by capillary action.

17. The method as set forth in claim 16 wherein the porous body is made of porous silica.

18. The method as set forth in any one of claims 15 to 17 wherein a moisture content of the green body is

less than about 50%, less than about 45%, at least about 30 wt%, at least about 35 wt%, at least about 40 wt%, at least about 45 wt%, from about 30 wt% to about 50 wt% or from about 35 wt% to about 45 wt%.

19. The method as set forth in any one of claims 15 to 18 wherein the green body is sintered at a temperature from about 1200°C to about 1800°C, from about 1300°C to about 1700°C, or from about 1300°C to about 1650°C.

20. The method as set forth in any one of claims 15 to 19 wherein the bottom channel, outer sidewall channel, and inner weir channel are each fluidly connected to each other.

21. The method as set forth in claim 20 wherein the bottom channel is rounded.

22. The method as set forth in claim 21 wherein the unitized crucible assembly includes a single layer bottom.

23. The method as set forth in any one of claims 15 to 22 wherein the unitized crucible assembly is transparent.

24. The method as set forth in any one of claims 15 to 23 wherein the unitized crucible assembly comprises:

a bottom;

an outer sidewall that extends upward from the bottom; and

an inner weir that extends upward from the bottom, the inner weir being disposed radially inward of the outer sidewall channel.

25. The method as set forth in any one of claims 15 to 24 wherein the mold comprises an inner weir peg that extends through the inner weir channel to form an opening in the inner weir of the unitized crucible assembly to allow silicon melt to pass through the inner weir.

26. The method as set forth in any one of claims 15 to 25 wherein the slip slurry and/or crucible mold are selected to form a unitized crucible assembly having a concentration of calcium of less than about 1 ppmw, a concentration of sodium of less than about 0.5 ppmw, a concentration of potassium of less than about 0.5 ppmw, a concentration of lithium of less than about 0.5 ppmw, and a concentration of iron of less than about 0.5 ppmw.

27. A crucible mold comprising:

a lower portion; and

an upper portion disposed above the lower portion, the upper portion forming:

a central weir channel; and

an inner weir channel;

wherein the upper portion and lower portion together form:

a bottom channel; and

a sidewall channel fluidly connected to the bottom channel, wherein the central weir channel and inner weir channel extend from the bottom channel.

28. The crucible mold as set forth in claim 27 wherein the upper portion comprises a flange, the flange resting on the lower portion.

29. The crucible mold as set forth in claim 27 or claim 28 wherein the crucible mold is porous.

30. The crucible mold as set forth in claim 29 wherein the crucible mold is made of porous silica.

31. The crucible mold as set forth in any one of claims 27 to 30 comprising a central weir peg that extends laterally across the central weir channel to form an opening in a central weir of a crucible formed from the mold.

32. The crucible mold as set forth in claim 31 comprising an inner weir peg that extends laterally across the inner weir channel to form an opening in an inner weir of a crucible formed from the mold.

33. The crucible mold as set forth in any one of claims 27 to 32 wherein the bottom channel is rounded.

34. The crucible mold as set forth in any one of claims 27 to 33 wherein the upper portion has a main body having lower surface and the lower portion has a main body having an upper surface, the lower and upper surfaces forming the bottom channel and the sidewall channel.

35. The crucible mold as set forth in claim 34 wherein the upper portion comprises a flange that extends from the main body of the upper portion, the flange resting on the main body of the lower portion.

36. The crucible mold as set forth in claim 34 or claim 35 wherein at least a portion of the lower surface is rounded and at least portion of the upper surface is rounded.

37. A crucible assembly comprising:

a bottom;

an outer sidewall that extends upward from the bottom;

a central weir that extends upward from the bottom; and

an inner weir that extends upward from the bottom, the central weir being disposed between the outer sidewall and the inner weir, wherein the bottom, outer sidewall, central weir and inner weir are unitized and are free of seams at (1) a joint between the outer sidewall and the bottom, (2) a joint between the central weir and the bottom, (3) a joint between the inner weir and the bottom.

38. The crucible assembly as set forth in claim 37 wherein the bottom is rounded.

39. The crucible assembly as set forth in claim 37 or claim 38 wherein the crucible assembly consists essentially of quartz.

40. The crucible assembly as set forth in any one of claims 37 to 39 wherein the crucible assembly has a concentration of calcium of less than about 1 ppmw, a concentration of sodium of less than about 0.5 ppmw, a concentration of potassium of less than about 0.5 ppmw, a concentration of lithium of less than about 0.5 ppmw, and a concentration of iron of less than about 0.5 ppmw.